



TO-92 Plastic-Encapsulate Transistors

MPSA55 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

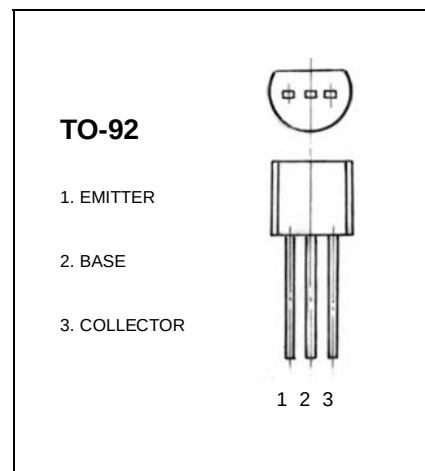
I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-BASE breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_B=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-60V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.25	V
Base-Emitter Saturation Voltage	V_{BE}	$V_{CE}=-1V, I_C=-100mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-1V, I_C=-100mA$ $f=100MHz$	50			MHz